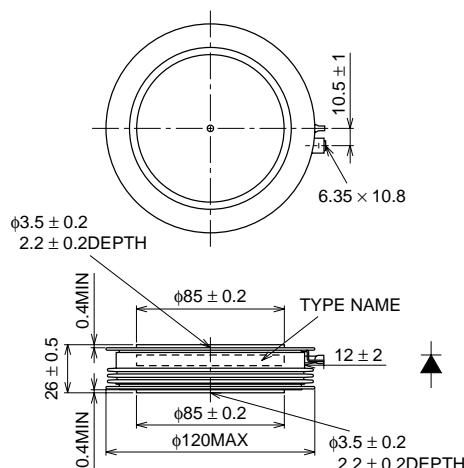


FD1500BV-90DAHIGH POWER, HIGH FREQUENCY,
PRESS PACK TYPE**FD1500BV-90DA**

- IF(AV) Average forward current 1500A
- VRMM Repetitive peak reverse voltage 4500V
- QRR Reverse recovery charge 3600 μ C
- Press pack type

OUTLINE DRAWING

Dimensions in mm

**APPLICATION**

Free wheel diode for GCT Thyristor
 High-power inverters
 Power supplies as high frequency rectifiers

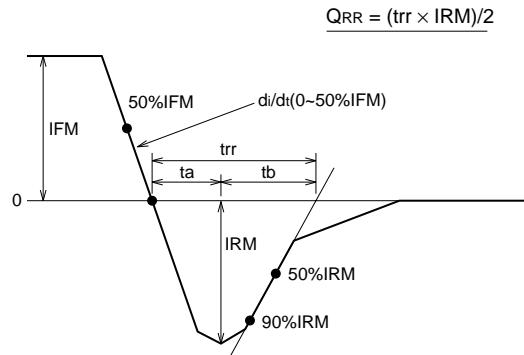
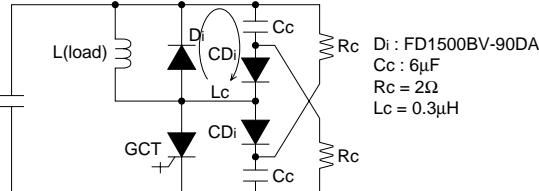
MAXIMUM RATINGS

Symbol	Parameter	Voltage class	Unit
VRMM	Repetitive peak reverse voltage	4500	V
VRSM	Non-repetitive peak reverse voltage	4500	V
VR(DC)	DC reverse voltage	3600	V
VLTDS	Long term DC stability voltage at 100FIT	3000	V

Symbol	Parameter	Conditions	Ratings	Unit
IF(RMS)	RMS forward current	Applied for all conduction angles	2350	A
IF(AV)	Average forward current	f = 60Hz, sine wave $\theta = 180^\circ$, Tf = 65°C	1500	A
IFSM	Surge forward current		30	kA
I ² t	Current-squared, time integration	One half cycle at 60Hz, Tj=125°C	3.7×10^6	A ² s
di/dt	Critical rate of rise of reverse recovery current	IFM = 1500A, VR ≤ 2250V, Tj = 125°C, With clamp circuit (see Fig. 1, 2)	2000	A/ μ s
T _j	Junction temperature		-20 ~ 125	°C
T _{stg}	Storage temperature		-40 ~ 150	°C
—	Mounting force required	(Recommended value 47kN)	39 ~ 55	kN
—	Weight	Typical 1220g	—	g

ELECTRICAL CHARACTERISTICS

Symbol	Parameter	Test conditions	Limits			Unit
			Min.	Typ.	Max.	
I _{RRM}	Repetitive peak reverse current	V _{RM} = 4500V, T _j = 125°C	—	—	150	mA
V _{FM}	Forward voltage	I _{FM} = 3400A, T _j = 125°C	—	—	3.5	V
Q _{RR}	Reverse recovery charge	I _{FM} = 1500A, d <i>i</i> /dt = 1000A/μs, V _R = 2250V,	—	—	3600	μC
E _{rec}	Reverse recovery loss	T _j = 125°C	—	8.0	—	J/P
t _b /t _a	Soft recovery rate	With clamp circuit (see Fig. 1, 2)	—	2	—	—
R _{th(j-f)}	Thermal resistance	Junction to fin	—	—	0.011	°C/W

Fig. 1 (Definition of reverse recovery waveform)**Fig. 2 (Reverse recovery test circuit)**

FD1500BV-90DAHIGH POWER, HIGH FREQUENCY,
PRESS PACK TYPE

PERFORMANCE CURVES

